



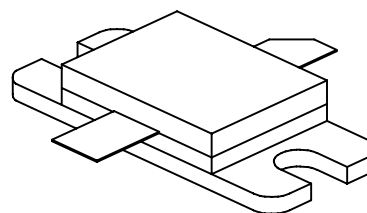
TPR 500A

500 Watts, 50 Volts, Pulsed
Avionics 1030 - 1090 MHz

GENERAL DESCRIPTION

The TPR 500A is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 1030-1090 MHz. The device has gold thin-film metallization and diffused ballasting for proven highest MTTF. The transistor includes input prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

CASE OUTLINE 55KT, STYLE 1



ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C² 1750 Watts

Maximum Voltage and Current

BVces Collector to Base Voltage 55 Volts

BVebo Emitter to Base Voltage 3.5 Volts

Ic Collector Current 40 Amps

Maximum Temperatures

Storage Temperature - 65 to + 200°C

Operating Junction Temperature + 200°C

ELECTRICAL CHARACTERISTICS @ 25 °C

| SYMBOL | CHARACTERISTICS | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|--------|-------------------------|-----------------|-----|-----|------|-------|
| Pout | Power Out | F = 1090 MHz | 500 | | | Watts |
| Pin | Power Input | Vcc = 50 Volts | | | 150 | Watts |
| Pg | Power Gain | PW = 10 μsec | 5.2 | | | dB |
| ηc | Collector Efficiency | DF = 1% | | 35 | | % |
| VSWR | Load Mismatch Tolerance | F = 1090 MHz | | | 10:1 | |

| | | | | | | |
|------------------|--------------------------------|------------------------|-----|--|-----|-------|
| BVebo | Emitter to Base Breakdown | Ie = 30 mA | 3.5 | | | Volts |
| BVces | Collector to Emitter Breakdown | Ic = 30 mA | 55 | | | Volts |
| hFE | DC - Current Gain | Ic = 500 mA, Vce = 5 V | 10 | | | |
| θjc ² | Thermal Resistance | | | | 0.1 | °C/W |

Note 1: At rated output power and pulse conditions

2: At rated pulse conditions

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